INFO	RMATION		
MODEL:	C-001R		
INFO. No. :	13A		
DATE:	Feb. 25. 2007		
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INTRODUCTION

- The contents is subject to change without notice.
 Please exchange the specification sheets regarding the product's warranty.
- 2. This sheet is not intended to guarantee or provide an approval of implementation of industrial patents.
- We have prepared this sheet as carefully as possible. If you find it incomplete or unsatisfactory in any respect, We would welcome your comments.

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This product listed here is designed as components or parts for electronics equipment in general consumer use. We do not expect that any of these products would be incorporated or otherwise used as a component or part for the equipment, which requires an extra high reliability, such as satellite, rocket and other space systems, and medical equipment, the functional purpose of which is to keep life.

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[1] Absolute maximum ratings

No.	Parameter	Symbol	Rating value	Note
1	Storage temperature	Tstg		Suppose to be within CI STD at +25 °C ± 3 °C.
2	Maximum drive level	GL	1 μW	

[2] Operating range

			Value			
No.	Parameter	Symbol	Min.	Тур.	Max.	Note
1	Operating range	Topr	-10 °C		+60 °C	
2	Drive level	DL		0.1 μW		
3	Vibration mode		Fundamental		1	

[3] Electrical characteristics

No.	Parameter	Symbol	Standard	Conditions	
1	Frequency	FL	32.768 kHz		
2	Frequency tolerance	Δf / f	± 5 ppm	CL = 12.5 pF $Ta = +25 \text{ °C} \pm 3 \text{ °C}$ $DL = 0.1 \mu\text{W}$ Excluding aging value	
3	Quality factor	Q	Min. 6.5×10^4		
4	Series resistance	Rı	Max. 35 K Ω		
5	Motional capacitance	C1	Typ. 2.1 fF	CI meter : Sanders 140-B DL = 1.0 µW	
6	Shunt capacitance	C ₀	Typ. 0.9 pF		
7	Turnover temperature	θТ	+25 °C ± 3 °C	Value calculated on temperature	
8	Parabolic coefficient	a	Max4.0 \times 10 ⁻⁸ / °C ²	+10, +25, +40 °C degree with C-MOS circuit.	
9	Insulation resistance	IR	Min. 500 MΩ	DC 100V, 60 sec. between terminals or terminal and case	
10	Aging		$\pm 3 \times 10^6$ / year	Ta = +25 °C ± 3 °C DL = 0.1 μW	
11	Against pressure		± 5 × 10 ⁻⁶	Frequency shift at case cramped.	

[4] Environmental characteristics

(The company evaluation condition We evaluate it by the following examination item and examination condition.)

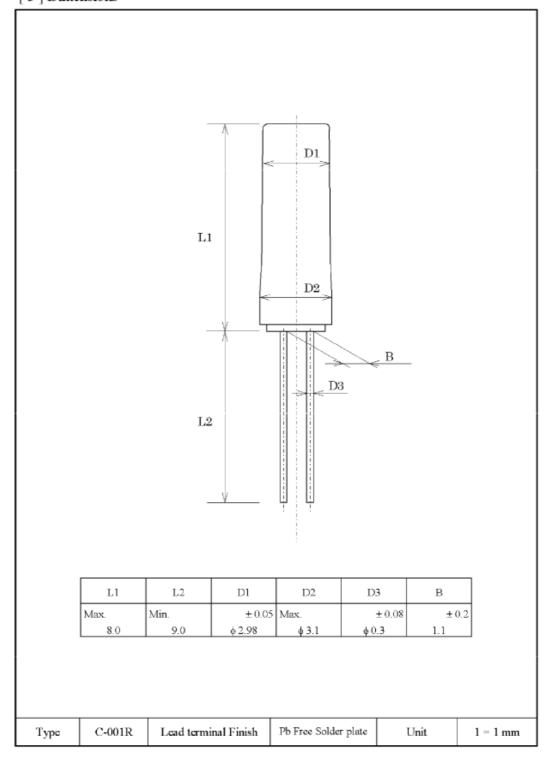
(IIII	company crandation condition - vic	I	rxamination item and examination condition.)	
No.	Item	Value *1 *2	Test Conditions	
		$\Delta f/f = [1 \times 10^{-6}]$		
			Free drop from 750 mm height on a hard	
1	Drop	± 5	wooden board for 3 times	
			(Board is thickness more than 30 mm)	
		+3	10 Hz to 55 Hz amplitude 0.75 mm	
2	Vibration		55 Hz to 500 Hz acceleration 98 m/s ²	
2	vioration	±3	$10 \text{ Hz} \rightarrow 500 \text{ Hz} \rightarrow 10 \text{ Hz}$ 15 min./cycle	
			6 h (2 hours, 3 directions)	
3	High temperature storage	± 5	+80 °C × 240 h	
4	Low temperature storage	± 5	-20 °C × 240 h	
Ľ	20 W temperature Storage			
5	Temperature cycle	± 5	-20 °C ↔ +80 °C	
Ľ	Temperature cycle	Τ.7	30 min. at each temp. 20 cycle	
	Resistance to soldering heat for		Dip wire termination on closer than 2 mm	
6	wire termination	±3	from the case into solder bath at	
	wire termination		+280 °C ± 10 °C for 5 s	
		±3	Pulling a wire termination with 10 N	
7	Tensile test on termination	No defect for wire	weight for 5 s	
		termination		
	Flexibility of termination	±3	A point 1 mm from the base is bent	
8		No defect for wire	following angle : +90° → -90° → 0°	
		termination	(R 0.5)	
		Termination must be	Dip termination into solder bath at	
9	Solderability	95 % covered with fresh	+240 °C ± 10 °C for 3 s	
		solder	(Using Rosin Flux)	

< Notes >

^{1. *1} Each test done independently.

^{2. *2} Measuring 2 h to 24 h later leaving in room temperature after each test.

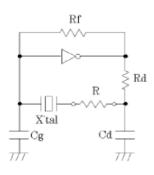
[5] Dimensions



[6] Notes

- If the temperature of the package exceeds +150 °C., the crystal resonator may be damaged or its characteristic may be impaired.
- Bending the lead too closely to the case or pulling the lead strongly may cause the hermetic glass seal to crack. If the lead needs to bend, please leave more than 0.5 mm from the lead to the case.
- Excessive pressure may cause leakage of hermetically. Please take caution not to give excessive press to the sealed part of the package.
- Excessive shock or vibration is not allowed. The internal crystal resonator may be damaged from machine shock during assembly. Please check conditions carefully prior to use.
- To avoid condensation, do not store or use in an environment where temperatures may change rapidly. We recommend that products be stored in an environment where temperature and humidity are normal.
- Products using a tuning fork crystal can not be guaranteed for ultrasonic cleaning because they may be damaged by resonance vibration.
- Applying excessive drive level to the crystal resonator may cause deterioration or damage. Circuit design must be such that the proper drive level is maintained.
- Unless adequate negative resistance is allocated in the oscillation circuit, start up time of oscillation may be increased or stopped. In order to avoid this, please provide enough negative resistance in the circuit design.

(How to check the negative resistance [-NR])



- Connect the resister (R) to the circuit in series with the crystal resonator.
- (2) Adjust (R) so that oscillation can start (or stop).
- (3) Measure (R) when oscillation just start (or stop) in above (2).
- (4) Get the negative resistance. [-NR] = R + CI value
- (5) Recommended [-NR] [-NR] > CI (Max.) × (5 to 10)